PCN Number:		2019	20191104001.1				PCN	l Da	ite:	Nov 13, 2019			
Title:	Conversion t	to TSMC	SMC 0.6/0.5um Hybrid Process										
Customer Contact:				PCN Manager			Dep	t:		Quality Services			
Proposed 1 st Ship Date:			Feb 13, 2020			Estimated Sample Availability:			nple	Date provided at sample request.			
Change Type:													
	nbly Site		Assembly Process Assembly Materials										
Design			Electrical Specification					<u>Ц</u>		echanical Specification			
Test S			Packing/Shipping/Labeling					<u> </u>	Test Process Wafer Bump Process				
	Bump Site Fab Site		Wafer Bump Material Wafer Fab Materials					\boxtimes		r Bump Process r Fab Process			
water	rab Site		Part number change						wate	I Fab Process			
				Notification									
Descriptio	n of Change:	:		- Troumed the		ctans							
metallizatio	n/SOG Etch B	Back pro	ces	nce the conver s to the TSMC ct Affected" se	0.5ur	n Tungs	curr ten p	ent lug	TSMC (back e	0.6um back end end process for the			
	Chang	ge Fror	n					Ch	ange '	То			
C	.6um TSMC B	ackend	Pro	cess		0.5	um T	SMO	C Backe	end Process			
IME	D layer: PEOX					IMD layer: PEOX+SACVD-OX+PEOX+SOG							
	Metal: Ti /	AlSiCu				dep. & Etch back+PEOX							
						Metal: Via Plug TiN/WCVD/AlCu /TiN							
Reason for Quality Imp													
		Fit Fo	Form, Function, Quality or Reliability (positive / negative):										
None.	d impact on	110, 10	, , , , , , , , , , , , , , , , , , ,										
	o product ide	entifica	atio	n resulting fr	om t	his noti	ficat	ion					
None.	o product lat	CITCITICE	10.0	ir resureing in	0111 €	1113 11001	ricat		•				
Product At	ffected:												
REF3112AI		REF313	ROAT	DBZR	RFF3	140TDD1			RFF	3225AIDBVTG4			
INC. STIZA		1101010		DDZIN	I VLI J	1 10 1 0 0			1 1 1	3223/(1887) 61			
DEE3112AT	DB7DG/	DEE313		DB7DC4	DEE3	140TDD2			DEE	323UVIDB/\b			
REF3112AI			30AI	DBZRG4		140TDD2			-	3230AIDBVR			
REF3112AI	DBZT	REF313	30AI 30AI	DBZT	REF3	212AIDB\	/R		REF	3230AIDBVT			
REF3112AI	DBZT DBZTG4	REF313	30AI 30AI 30AI	DBZT DBZTG4	REF3	212AIDB\ 212AIDB\	/R /T		REF	3230AIDBVT 3230AIDBVTG4			
REF3112AI REF3112AI REF3120AI	DBZT DBZTG4 DBZR	REF313 REF313	30AI 30AI 30AI 33AI	DBZT DBZTG4 DBZR	REF3 REF3	212AIDB\ 212AIDB\ 212AIDB\	/R /T /TG4		REF REF	3230AIDBVT 3230AIDBVTG4 3233AIDBVR			
REF3112AI REF3112AI REF3120AI	DBZT DBZTG4 DBZR DBZRG4	REF313 REF313 REF313	30AI 30AI 30AI 33AI 33AI	DBZT DBZTG4 DBZR DBZT	REF3 REF3 REF3	212AIDB\ 212AIDB\ 212AIDB\ 220AIDB\	/R /T /TG4 /R		REF REF REF	G3230AIDBVT G3230AIDBVTG4 G3233AIDBVR G3233AIDBVT			
REF3112AI REF3112AI REF3120AI REF3120AI	DBZT DBZTG4 DBZR DBZRG4 DBZTG4	REF313 REF313 REF313 REF313	30AI 30AI 30AI 33AI 33AI 33AI	DBZT DBZTG4 DBZR DBZT DBZT	REF3 REF3 REF3 REF3	212AIDB\ 212AIDB\ 212AIDB\ 220AIDB\ 220AIDB\	/R /T /TG4 /R /T		REF REF REF REF	G3230AIDBVT G3230AIDBVTG4 G3233AIDBVR G3233AIDBVT G3233AIDBVTG4			
REF3112AI REF3112AI REF3120AI REF3120AI REF3120AI	DBZT DBZTG4 DBZR DBZRG4 DBZTT DBZTG4	REF313 REF313 REF313 REF313 REF314	30AI 30AI 30AI 33AI 33AI 33AI 40AI	DBZT DBZTG4 DBZR DBZT DBZT DBZTG4 DBZR	REF3 REF3 REF3 REF3 REF3	212AIDB\ 212AIDB\ 212AIDB\ 212AIDB\ 220AIDB\ 220AIDB\ 220AIDB\	/R /T /TG4 /R /T /TG4		REF REF REF REF REF	G3230AIDBVT G3230AIDBVTG4 G3233AIDBVR G3233AIDBVT G3233AIDBVTG4 G3240AIDBVR			
REF3112AI REF3112AI REF3120AI REF3120AI	DBZT DBZTG4 DBZR DBZRG4 DBZTT DBZTG4	REF313 REF313 REF313 REF313 REF314	30AI 30AI 30AI 33AI 33AI 33AI 40AI	DBZT DBZTG4 DBZR DBZT DBZT	REF3 REF3 REF3 REF3 REF3	212AIDB\ 212AIDB\ 212AIDB\ 220AIDB\ 220AIDB\	/R /T /TG4 /R /T /TG4		REF REF REF REF REF	G3230AIDBVT G3230AIDBVTG4 G3233AIDBVR G3233AIDBVT G3233AIDBVTG4			
REF3112AI REF3112AI REF3120AI REF3120AI REF3120AI	DBZT DBZTG4 DBZR DBZRG4 DBZT DBZT DBZTG4 DBZTG4 DBZR	REF313 REF313 REF313 REF313 REF314	30AI 30AI 30AI 33AI 33AI 40AI	DBZT DBZTG4 DBZR DBZT DBZTG4 DBZTG4 DBZR DBZRG4	REF3 REF3 REF3 REF3 REF3 REF3	212AIDB\ 212AIDB\ 212AIDB\ 212AIDB\ 220AIDB\ 220AIDB\ 220AIDB\	/R /T /TG4 /R /T /TG4		REF REF REF REF REF	G3230AIDBVT G3230AIDBVTG4 G3233AIDBVR G3233AIDBVT G3233AIDBVTG4 G3240AIDBVR			
REF3112AI REF3112AI REF3120AI REF3120AI REF3120AI REF3125AI	DBZT DBZTG4 DBZRG4 DBZTG4 DBZTG4 DBZTG4 DBZR	REF313 REF313 REF313 REF314 REF314 REF314	30AI 30AI 33AI 33AI 33AI 40AI 40AI	DBZT DBZTG4 DBZR DBZT DBZTG4 DBZTG4 DBZR DBZRG4	REF3 REF3 REF3 REF3 REF3 REF3 REF3	212AIDB' 212AIDB' 212AIDB' 220AIDB' 220AIDB' 220AIDB' 225AIDB'	/R /T /TG4 /R /T /TG4 /R		REF REF REF REF REF REF	G3230AIDBVT G3230AIDBVTG4 G3233AIDBVR G3233AIDBVT G3233AIDBVTG4 G3240AIDBVR G3240AIDBVRG4			

Automotive New Product Qualification Summary

(As per AEC-Q100 and JEDEC Guidelines)

Q100H Grade-1 qual for REF31XXAQDBZRQ1 (TSMC-WF2 / 0.5/0.6-DPDM) in HNT using 3-pin SOT pkg Approved 28-Mar-2017

Product Attributes

Attributes	Qual Device: REF3133AQDBZRQ1	Qual Device: REF3112AQDBZRQ1	Qual Device: REF3120AQDBZRQ1	Qual Device: REF3125AQDBZRQ1	Qual Device: REF3130AQDBZRQ1	Qual Device: REF3140AQDBZRQ1	QBS Process Reference: OPA356AQDBVRQ1
Operating Temp Range	-40 to +125 C						
Automotive Grade Level	Grade 1						
Product Function	Power Management	Signal Chain					
Wafer Fab Supplier	TSMC-WF2						
Die Revision	E	E	E	E	E	E	-
Assembly Site	HNT	HNT	HNT	HNT	HNT	HNT	NFME
Package Type	SOT						
Package Designator	DBZ	DBZ	DBZ	DBZ	DBZ	DBZ	DBV
Ball/Lead Count	3	3	3	3	3	3	5

- QBS: Qual By Similarity
 Qual Device REF3112AQDBZRQ1 is qualified at LEVEL2-260C
 Qual Devices qualified at LEVEL3-260C: REF3120AQDBZRQ1, REF3130AQDBZRQ1, REF3140AQDBZRQ1, REF3125AQDBZRQ1, REF3133AQDBZRQ1

Qualification Results
Data Displayed as: Number of lots / Total sample size / Total failed

 Qual Device:
 Qual Device:<

PC	A1	JEDEC J-STD- 020 JESD22- A113	3	77	Automotive Preconditioning	Level 2-260C peak	3/all/0	-	-	-	-	-	3/all/0
HAST	A2	A110	3	77	Biased HAST, 130C/85%RH	96 Hours	3/231/0	-	-	-	-	-	3/231/0
AC	A3	A102	3	77	Autoclave 121C	96 Hours	3/231/0	-	-	-	-	-	3/230/0
TC	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	3/231/0	-		-	-	-	3/230/0
TC-BP	A4	MIL-STD883 Method 2011	1	30	Post Temp. Cycle Bond Pull	500 Cycles	1/30/0	-	-	-	-	-	1/30/0
PTC	A5	JEDEC JESD22- A105	1	45	Power Temperature Cycle	1000 Cycles	N/A	N/A	N/A	N/A	N/A	N/A	-
HTSL	A6	JEDEC JESD22- A103	1	45	High Temp Storage Bake 175C	500 Hours	1/45/0	-	-	-	-	-	1/45/0
Test Grou	рВ−А	ccelerated Lifetime	Simulati	on Tes	ts								
HTOL	B1	JEDEC JESD22-	3	77	Life Test, 125C	1000 Hours	3/231/0	_		_	_	-	3/231/0
ELFR	B2	A108	3	800		48 Hours	-	_	_	-	-	-	3/2400/0
EDR	B3		3	77	NIVM Endurance Data Retention		N/A	N/A	N/A	N/A	N/A	N/A	-
					and Operational Life								
Test Grow	n C _ Pa	ckane Assembly Int	enrity To	ooto									
	$\overline{}$	ickage Assembly Int		$\overline{}$									
WBS	C1	AEC Q100-001 MIL-STD883	1		Bond Shear (Cpk>1.67)	Wires	1/30/0	-	-	-	-	-	-
WBP	C2	Method 2011	1	30	Bond Pull (Cpk>1.67)	Wires	1/30/0	-	-	-	-	-	-
SD	C3	JEDEC JESD22- B102	1	15	Solderability (>95% Coverage)	Steam aging 8 hrs	-	-	-	-	-	-	1/15/0*
PD	C4	JEDEC JESD22- B100 and B108	3	10	Physical Dimensions (Cpk>1.67)	=	3/30/0	=	-	-	-	=	-
SBS	C5	AEC Q100-010	3	50	Solder Ball Shear (Cpk>1.67)	Post HTSL/Bump	NA	-	-	-	-	-	-
		JEDEC JESD22-					NA NA						
LI	C6	B105	1	50	Lead Integrity	Leads	No.	-	-	-	-	-	-
				50	Lead Integrity	Leads	No.						
		B105			Lead Integrity Electromigration	Leads 	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group	D – Die F	B105 Fabrication Reliability T		-		Leads 	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology
Test Group EM	D – Die F	B105 Fabrication Reliability T JESD61		-	Electromigration Time Dependent Dielectric	Leads	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology
EM TDDB	D – Die F	B105 Fabrication Reliability T JESD61 JESD35		-	Electromigration Time Dependent Dielectric Breakdown	Leads	Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology
Test Group EM TDDB HCI NBTI	D - Die F - Di	B105 B105 B105 B105 B105 B105 B105 B105	ests	-	Electromigration Time Dependent Dielectric Break down Hot Injection Carrier	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements Completed Per Process Technology
EM TDDB HCI NBTI SM Test Group	D - Die F - Di	B105 abrication Reliability 1 JESD61 JESD65 JESD60 & 28 ectrical Verification	ests	-	Electromigration Time Dependent Dielectric Breakdown Hot Injection Carrier Negative Bias Temperature Instability Stress Migration	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group EM TDDB HCI NBTI	D - Die F - Di	B105 B105 B105 B105 B105 B105 B105 B105	ests	-	Electromigration Time Dependent Dielectric Breakdown Hot Injection Carrier Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements Completed Per Process Technology Tequirements	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements Completed Per Process Technology
EM TDDB HCI NBTI SM Test Group	D - Die F - Di	B105 abrication Reliability 1 JESD61 JESD65 JESD60 & 28 ectrical Verification	ests	3	Electromigration Time Dependent Dielectric Breakdown Hot Injection Carrier Negative Bias Temperature Instability Stress Migration	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
EM TDDB HCI NBTI SM Test Group	D1 D1 D2 D3 D4 D5 E- Electron	B105 abrication Reliability J JESD61 JESD35 JESD60 & 28	ests	3 3 3 3	Electromigration Time Dependent Dielectric Break down Hot Injection Carrier Negative Bias Temperature Instability Stress Migration ESD - HBM	2000 V 500 V (all pins)	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements Completed Per Process Technology Requirements
EM TDDB HCI NBTI SM Test Group HBM CDM	D - Die F D D D D D D D D D	B105 abrication Reliability T JESD61 JESD65 JESD60 & 28	ests	3 3 3 6	Electromigration Time Dependent Dielectric Breakdown Hot Injection Carrier Negative Bias Temperature Instability Stress Migration ESD - HBM ESD - CDM		Completed Per Process Technology Requirements 100 Per Process Technology Requirements 11/3/0 11/3/0	Completed Per Process Technology Requirements 17310	Completed Per Process Technology Requirements 173/0 1/3/0	Completed Per Process Technology Requirements 173/10	Completed Per Process Technology Requirements 1/3/0	Completed Per Process Technology Requirements 173/0	Completed Per Process Technology Requirements 1/3/0

A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST &TC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40°C to +150°C

Grade 1 (or Q): -40°C to +125°C

Grade 2 (or T): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL. ED

Room/Hot: THB/HAST, TC/PTC, HTSL, ELFR, ESD & LU

Room: AC/uHAST
Green/Pb-free Status:
Qualified Pb-Free (SMT) and Green

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